74AHC595; 74AHCT595

8-bit serial-in/serial-out or parallel-out shift register with output latches; 3-state

Rev. 03 — 25 April 2008 Product data sheet

1. General description

The 74AHC595; 74AHCT595 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74AHC595; 74AHCT595 is an 8-stage serial shift register with a storage register and 3-state outputs. The shift register has separate clocks.

Data is shifted on the positive-going transitions of the shift register clock input (SHCP). The data in each register is transferred to the storage register on a positive-going transition of the storage register clock input (STCP). If both clocks are connected together, the shift register will always be one clock pulse ahead of the storage register.

The shift register has a serial input (DS) and a serial standard output (Q7S) for cascading. It is also provided with asynchronous reset (active LOW) for all 8 shift register stages. The storage register has 8 parallel 3-state bus driver outputs. Data in the storage register appears at the output whenever the output enable input ($\overline{OE}$) is LOW.

2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
  - For 74AHC595: CMOS level
  - For 74AHCT595: TTL level
- ESD protection:
  - HBM EIA/JESD22-A114E exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
  - CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Applications

- Serial-to-parallel data conversion
- Remote control holding register

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	**Name**	**Description**	**Version**
74AHC595				
74AHC595D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHC595PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74AHC595BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74AHCT595				
74AHCT595D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHCT595PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

5. Functional diagram

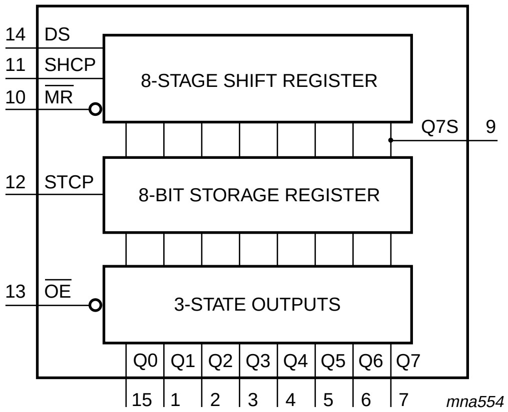


Fig 1. Functional diagram

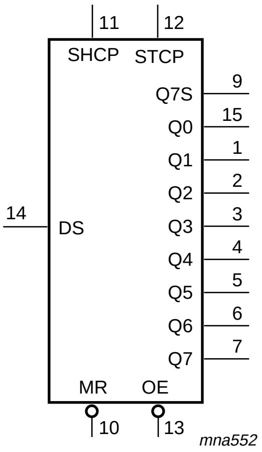


Fig 2. Logic symbol

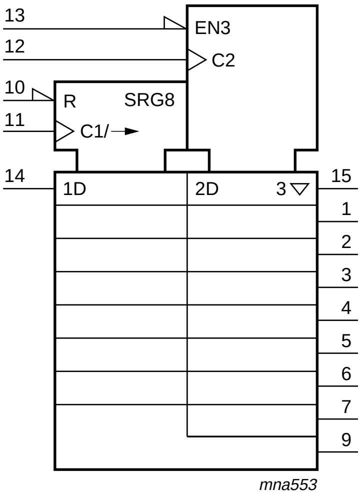


Fig 3. IEC logic symbol

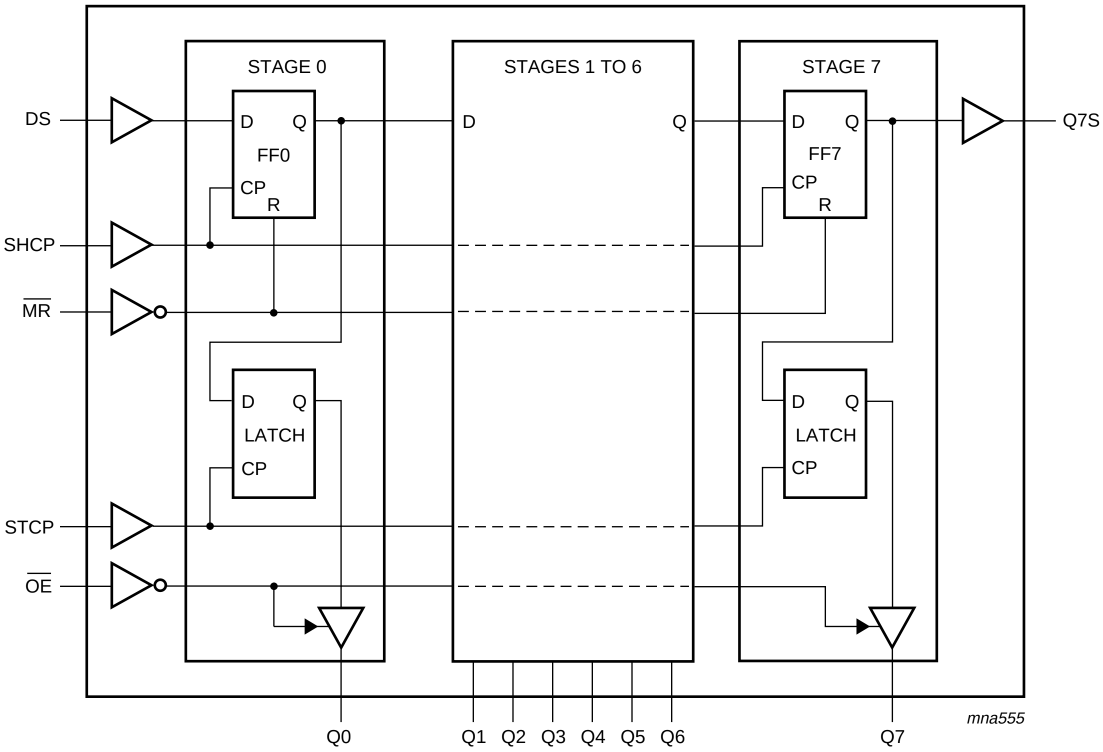


Fig 4. Logic diagram

6. Pinning information

6.1 Pinning

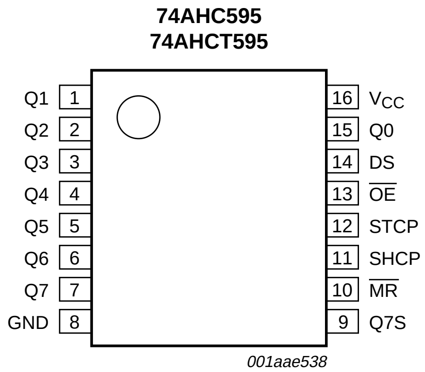


Fig 5. Pin configuration SO16 and TSSOP16

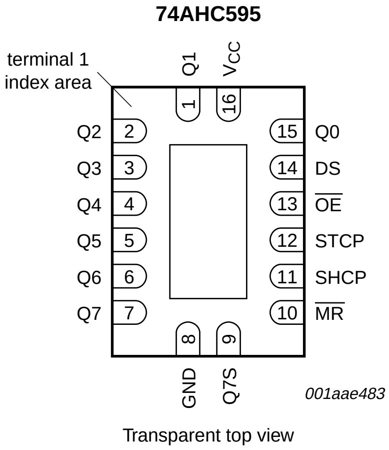


Fig 6. Pin configuration DHVQFN16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Q1	1	parallel data output 1
Q2	2	parallel data output 2
Q3	3	parallel data output 3
Q4	4	parallel data output 4
Q5	5	parallel data output 5
Q6	6	parallel data output 6
Q7	7	parallel data output 7
GND	8	ground (0 V)
Q7S	9	serial data output
$\overline{\text{MR}}$	10	master reset (active LOW)
SHCP	11	shift register clock input
STCP	12	storage register clock input
$\overline{\text{OE}}$	13	output enable input (active LOW)
DS	14	serial data input
Q0	15	parallel data output 0
V_{CC}	16	supply voltage

7. Functional description

Table 3. Function table[1]

Control				Input	Output		Function
SHCP	**STCP**	**$\overline{OE}$**	**$\overline{MR}$**	**DS**	**Q7S**	**Qn**	
X	X	L	L	X	L	NC	a LOW-level on $\overline{MR}$ only affects the shift registers
X	↑	L	L	X	L	L	empty shift register loaded into storage register
X	X	H	L	X	L	Z	shift register clear; parallel outputs in high-impedance OFF-state
↑	X	L	H	H	Q6S	NC	logic HIGH-level shifted into shift register stage 0. Contents of all shift register stages shifted through, e.g. previous state of stage 6 (internal Q6S) appears on the serial output (Q7S).
X	↑	L	H	X	NC	QnS	contents of shift register stages (internal QnS) are transferred to the storage register and parallel output stages
↑	↑	L	H	X	Q6S	QnS	contents of shift register shifted through; previous contents of the shift register is transferred to the storage register and the parallel output stages

[1] H = HIGH voltage state;
L = LOW voltage state;
↑ = LOW-to-HIGH transition;
X = don't care;
NC = no change;
Z = high-impedance OFF-state.

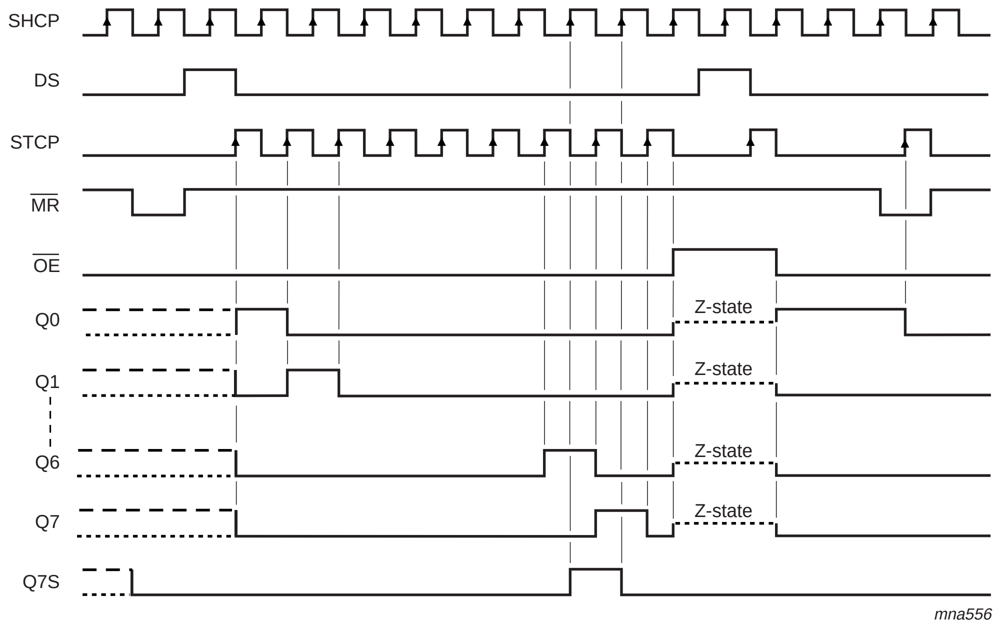


Fig 7. Timing diagram

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
V_I	input voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1]	–20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	–20	+20	mA
I_O	output current	$V_O = -0.5$ V to (V_{CC} + 0.5 V)		–25	+25	mA
I_{CC}	supply current			-	+75	mA
I_{GND}	ground current			–75	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

9. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC595						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.0 V to 3.6 V	-	-	100	ns/V
		V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT595						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC595										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –50 µA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 µA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 50 µA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
C_I	input capacitance		-	3	10	-	10	-	10	pF
74AHCT595										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 0$ V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	±0.25	-	±2.5	-	±10	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	4.0	-	40	-	80	µA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $I_O = 0$ A; $V_{CC} = 4.5$ V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	3	10	-	10	-	10	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC595										
t_{pd}	propagation delay	SHCP to Q7S; see Figure 8 [2]								
		V_{CC} = 3.0 V to 3.6 V								
		C_L = 15 pF	-	5.7	13.0	1.0	15.0	1.0	16.5	ns
		C_L = 50 pF	-	7.7	16.5	1.0	18.5	1.0	20.1	ns
		V_{CC} = 4.5 V to 5.5 V								
		C_L = 15 pF	-	4.0	8.2	1.0	9.4	1.0	10.5	ns
		C_L = 50 pF	-	5.4	10.0	1.0	11.4	1.0	12.5	ns
		STCP to Qn; see Figure 9 [2]								
		V_{CC} = 3.0 V to 3.6 V								
		C_L = 15 pF	-	5.9	11.9	1.0	13.5	1.0	15.0	ns
		C_L = 50 pF	-	7.7	15.4	1.0	17.0	1.0	18.5	ns
		V_{CC} = 4.5 V to 5.5 V								
		C_L = 15 pF	-	4.2	7.4	1.0	8.5	1.0	9.5	ns
		C_L = 50 pF	-	5.5	9.0	1.0	10.5	1.0	11.5	ns
		$\overline{MR}$ to Q7S; see Figure 11 [3]								
		V_{CC} = 3.0 V to 3.6 V								
		C_L = 15 pF	-	5.9	12.8	1.0	13.7	1.0	15.0	ns
		C_L = 50 pF	-	7.4	16.3	1.0	17.2	1.0	18.7	ns
		V_{CC} = 4.5 V to 5.5 V								
		C_L = 15 pF	-	4.4	8.0	1.0	9.1	1.0	10.0	ns
		C_L = 50 pF	-	5.6	10.0	1.0	11.1	1.0	12.0	ns
t_{en}	enable time	$\overline{OE}$ to Qn; see Figure 12 [4]								
		V_{CC} = 3.0 V to 3.6 V								
		C_L = 15 pF	-	5.6	11.5	1.0	13.5	1.0	15.0	ns
		C_L = 50 pF	-	7.4	15.0	1.0	17.0	1.0	18.5	ns
		V_{CC} = 4.5 V to 5.5 V								
		C_L = 15 pF	-	4.0	8.6	1.0	10.0	1.0	11.0	ns
		C_L = 50 pF	-	5.3	10.6	1.0	12.0	1.0	13.0	ns
t_{dis}	disable time	$\overline{OE}$ to Qn; see Figure 12 [5]								
		V_{CC} = 3.0 V to 3.6 V								
		C_L = 15 pF	-	5.4	11.0	1.0	13.0	1.0	14.5	ns
		C_L = 50 pF	-	8.7	15.7	1.0	16.2	1.0	17.5	ns
		V_{CC} = 4.5 V to 5.5 V								
		C_L = 15 pF	-	3.8	8.0	1.0	9.5	1.0	10.5	ns
		C_L = 50 pF	-	5.8	10.3	1.0	11.0	1.0	12.0	ns

Table 7. Dynamic characteristics *…continued*
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
f_{max}	maximum frequency	SHCP or STCP; see Figure 8 and 9								
		V_{CC} = 3.0 V to 3.6 V	80	125	-	60	-	40	-	MHz
		V_{CC} = 4.5 V to 5.5 V	130	170	-	110	-	90	-	MHz
t_W	pulse width	SHCP HIGH or LOW; see Figure 8								
		V_{CC} = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V_{CC} = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see Figure 9								
		V_{CC} = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V_{CC} = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
		$\overline{MR}$ LOW; see Figure 11								
		V_{CC} = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V_{CC} = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
t_{su}	set-up time	DS to SHCP; see Figure 9								
		V_{CC} = 3.0 V to 3.6 V	3.5	-	-	3.5	-	3.5	-	ns
		V_{CC} = 4.5 V to 5.5 V	3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see Figure 10								
		V_{CC} = 3.0 V to 3.6 V	8.5	-	-	8.5	-	8.5	-	ns
		V_{CC} = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
t_h	hold time	DS to SHCP; see Figure 10								
		V_{CC} = 3.0 V to 3.6 V	1.5	-	-	1.5	-	1.5	-	ns
		V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	ns
t_{rec}	recovery time	$\overline{MR}$ to SHCP; see Figure 11								
		V_{CC} = 3.0 V to 3.6 V	3.0	-	-	3.0	-	3.0	-	ns
		V_{CC} = 4.5 V to 5.5 V	2.5	-	-	2.5	-	2.5	-	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC} [6] [7]	-	180	-	-	-	-	-	pF
74AHCT595; V_{CC} = 4.5 V to 5.5 V										
t_{pd}	propagation delay	SHCP to Q7S; see Figure 8 [2]								
		C_L = 15 pF	-	3.8	8.2	1.0	9.0	1.0	10.0	ns
		C_L = 50 pF	-	5.2	10.0	1.0	11.0	1.0	12.0	ns
		STCP to Qn; see Figure 9 [2]								
		C_L = 15 pF	-	4.0	7.4	1.0	8.5	1.0	9.5	ns
		C_L = 50 pF	-	5.3	9.0	1.0	10.5	1.0	11.5	ns
		$\overline{MR}$ to Q7S; see Figure 11 [3]								
		C_L = 15 pF	-	4.6	8.2	1.0	9.5	1.0	10.5	ns
		C_L = 50 pF	-	5.8	10.5	1.0	11.5	1.0	12.5	ns

Table 7. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
t_{en}	enable time	$\overline{OE}$ to Qn; see Figure 12 [4]								
		C_L = 15 pF	-	4.8	9.0	1.0	11.0	1.0	12.0	ns
		C_L = 50 pF	-	6.2	11.6	1.0	13.0	1.0	14.5	ns
t_{dis}	disable time	$\overline{OE}$ to Qn; see Figure 12 [5]								
		C_L = 15 pF	-	3.6	6.9	1.0	8.0	1.0	9.0	ns
		C_L = 50 pF	-	5.8	10.3	1.0	11.0	1.0	12.0	ns
f_{max}	maximum frequency	SHCP and STCP; see Figure 8 and 9	130	170	-	110	-	90	-	MHz
t_W	pulse width	SHCP HIGH or LOW; see Figure 8	5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see Figure 9	5.0	-	-	5.0	-	5.0	-	ns
		$\overline{MR}$ LOW; see Figure 11	5.0	-	-	5.0	-	5.0	-	ns
t_{su}	set-up time	DS to SHCP; see Figure 9	3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see Figure 10	5.0	-	-	5.0	-	5.0	-	ns
t_h	hold time	DS to SHCP; see Figure 10	2.0	-	-	2.0	-	2.0	-	ns
t_{rec}	recovery time	$\overline{MR}$ to SHCP; see Figure 11	3.0	-	-	3.0	-	3.0	-	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC} [6] [7]	-	190	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage.

[2] t_{pd} is the same as t_{PHL} and t_{PLH}.

[3] t_{pd} is the same as t_{PHL} only.

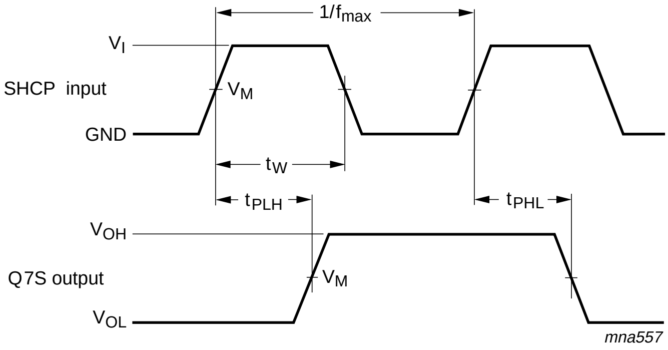
[4] t_{en} is the same as t_{PZL} and t_{PZH}.

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V.

[7] All 9 outputs switching.

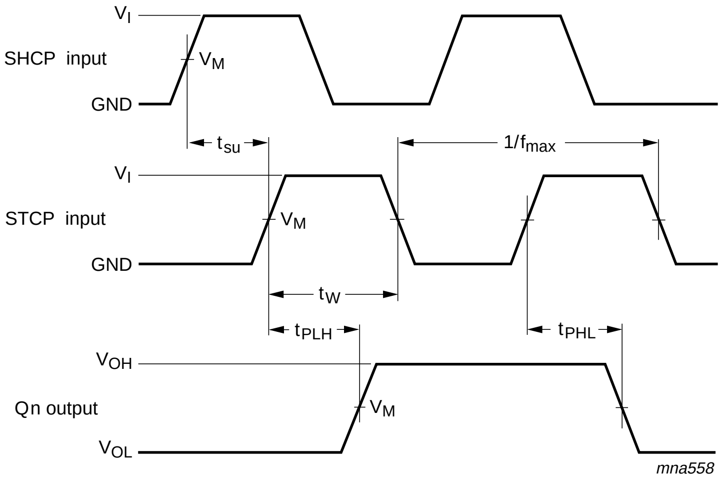
12. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

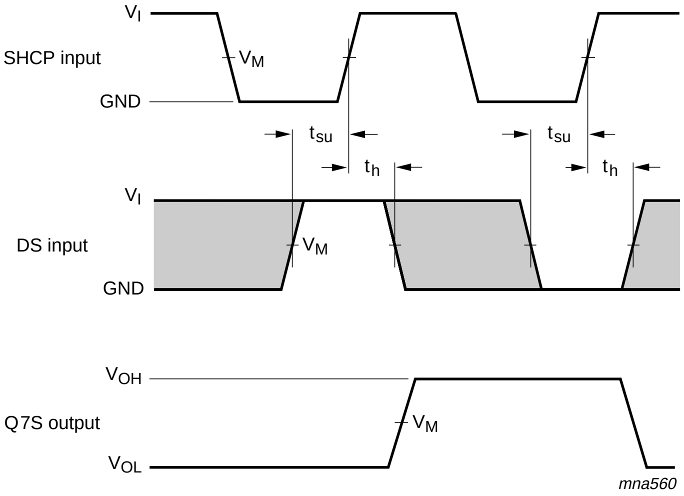
Fig 8. Shift clock pulse, maximum frequency and input to output propagation delays



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. Storage clock to output propagation delays

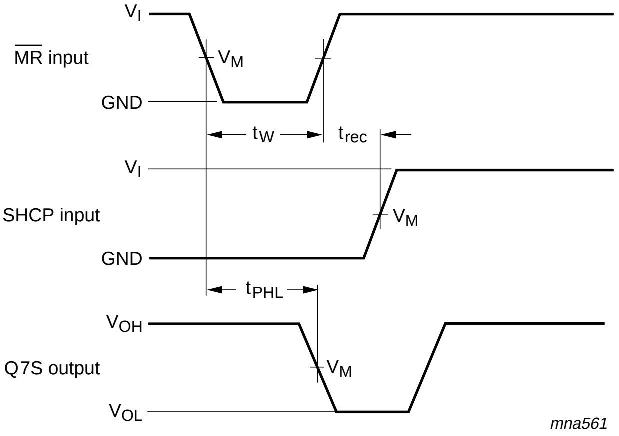


Measurement points are given in Table 8.

The shaded areas indicate when the input is permitted to change for predictable output performance.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

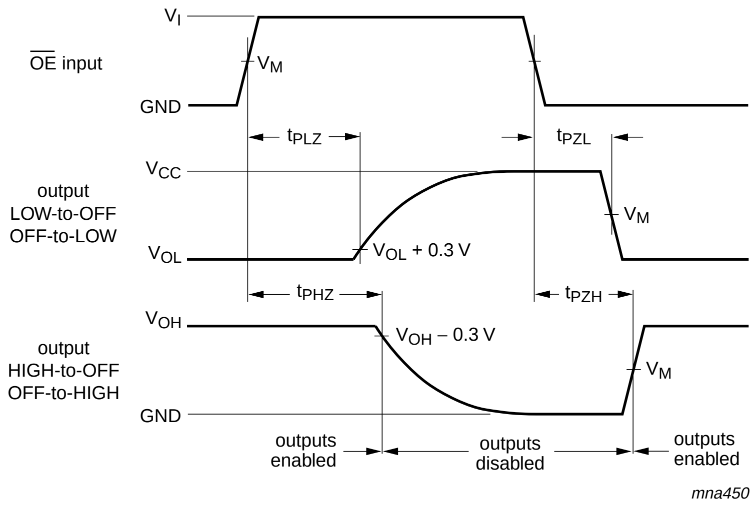
Fig 10. Data set-up and hold times



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 11. Master reset to output propagation delays



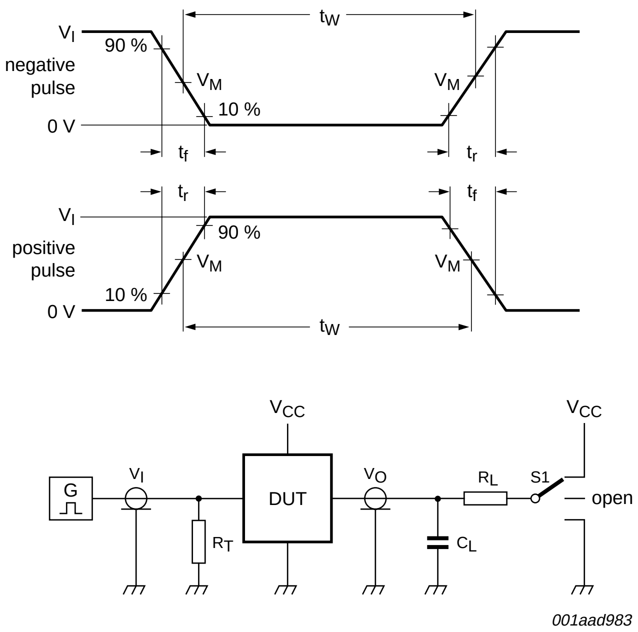
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 12. Enable and disable times

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74AHC595	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT595	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 9.

Definitions for test circuit:

C_L = load capacitance including jig and probe capacitance.

R_L = load resistance.

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

S1 = test selection switch.

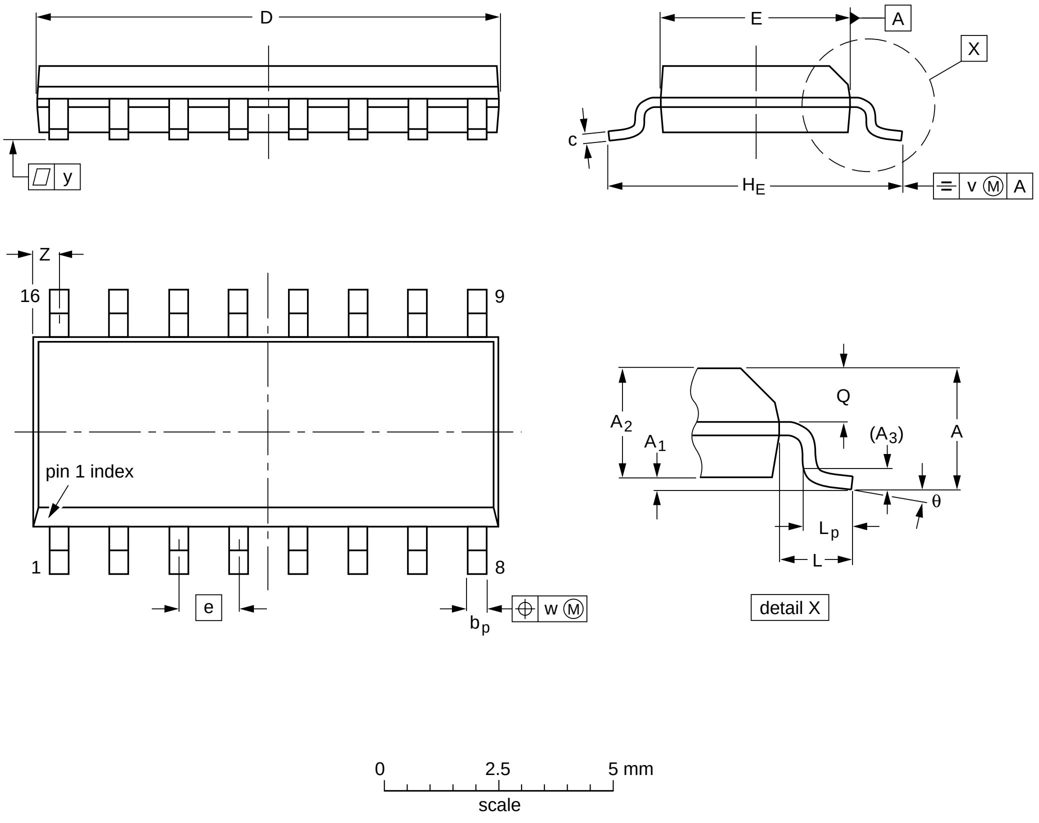
Fig 13. Load circuitry for switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC595	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74AHCT595	3.0 V	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

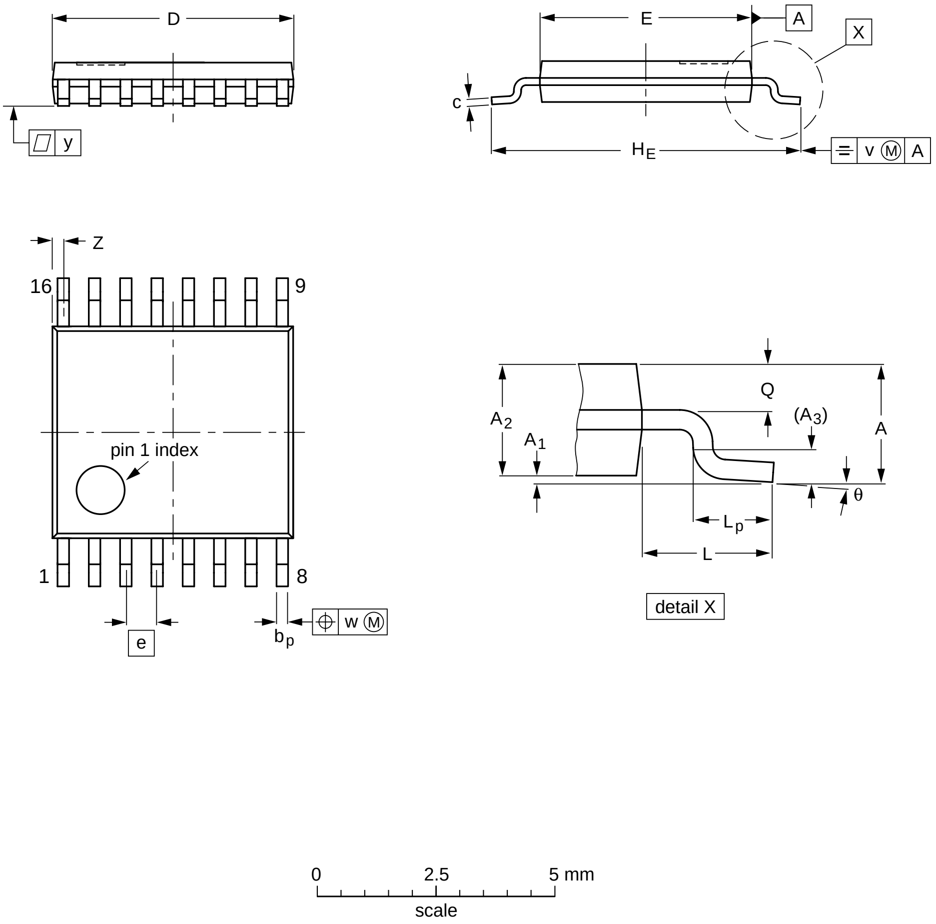
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 14. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A$_1$	A$_2$	A$_3$	b$_p$	c	D (1)	E (2)	e	H$_E$	L	L$_p$	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

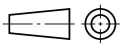
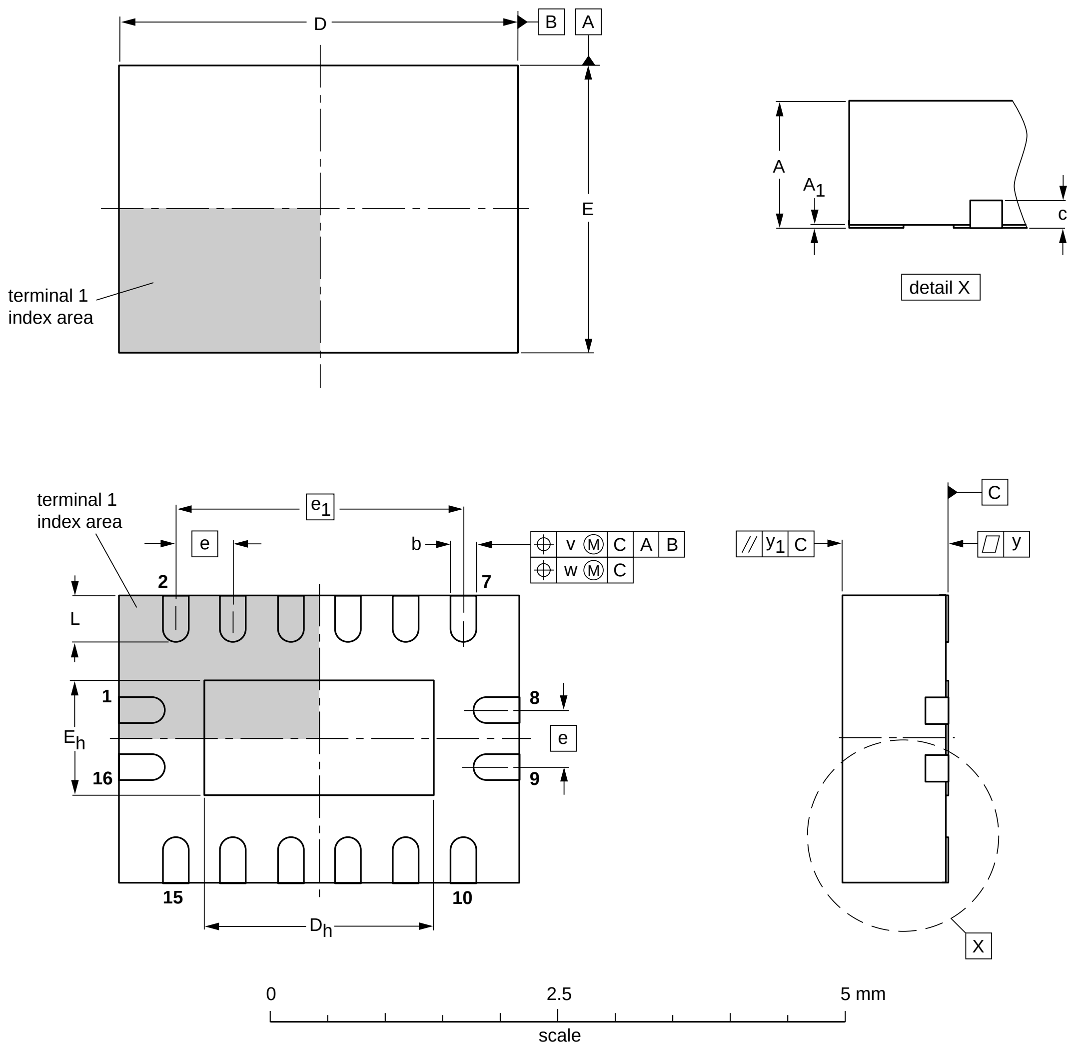
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 15. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max.	A_1	b	c	$D^{(1)}$	D_h	$E^{(1)}$	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 16. Package outline SOT763-1 (DHVQFN16)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT595_3	20080425	Product data sheet	-	74AHC_AHCT595_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 6: conditions for the input leakage current have been changed.			
74AHC_AHCT595_2	20060323	Product data sheet	-	74AHC_AHCT595_1
74AHC_AHCT595_1	20000315	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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